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## FAIRCHILD

SEMICONDUCTOR®

# SGP23N60UFD

## **Ultra-Fast IGBT**

## **General Description**

Fairchild's UFD series of Insulated Gate Bipolar Transistors (IGBTs) provides low conduction and switching losses. The UFD series is designed for applications such as motor control and general inverters where high speed switching is a required feature.

## Features

- High speed switching
- Low saturation voltage :  $V_{CE(sat)} = 2.1 \text{ V} @ I_C = 12 \text{ A}$
- High input impedance
- CO-PAK, IGBT with FRD : t<sub>rr</sub> = 42ns (typ.)

## **Applications**

AC & DC motor controls, general purpose inverters, robotics, and servo controls.



## Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Description       Collector-Emitter Voltage		I Description		Description SGP23N60UFD	
V <sub>CES</sub>			or-Emitter Voltage 600			
V <sub>GES</sub>	Gate-Emitter Voltage		± 20	V		
	Collector Current	@ T <sub>C</sub> = 25°C	23	A		
l <sub>C</sub>	Collector Current	@ T <sub>C</sub> = 100°C	12	A		
I <sub>CM (1)</sub>	Pulsed Collector Current		92	А		
I <sub>F</sub>	Diode Continuous Forward Current @ T <sub>C</sub> = 100°C		12	A		
I <sub>EM</sub>	Diode Maximum Forward Current		92	А		
P <sub>D</sub>	Maximum Power Dissipation	@ T <sub>C</sub> = 25°C	100	W		
	Maximum Power Dissipation	@ T <sub>C</sub> = 100°C	40	W		
TJ	Operating Junction Temperature		-55 to +150	°C		
T <sub>stg</sub>	Storage Temperature Range		-55 to +150	°C		
TL	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds		300	°C		

Notes : (1) Repetitive rating : Pulse width limited by max. junction temperature

## **Thermal Characteristics**

Symbol	Parameter	Тур.	Max.	Units
R <sub>θJC</sub> (IGBT)	Thermal Resistance, Junction-to-Case		1.2	°C/W
R <sub>0JC</sub> (DIODE)	Thermal Resistance, Junction-to-Case		2.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient		62.5	°C/W

IGBT

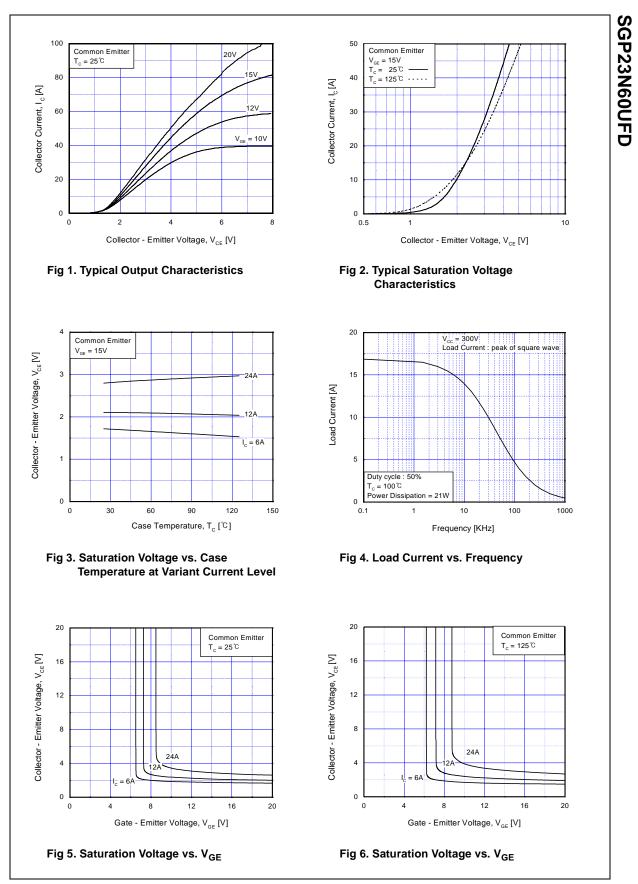
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Cha	racteristics					
BV <sub>CES</sub>	$V_{\rm S}$ Collector-Emitter Breakdown Voltage V <sub>GE</sub> = 0V, I <sub>C</sub> = 250uA		600			V
ΔB <sub>VCES</sub> / ΔT <sub>J</sub>	Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$		0.6		V/∘C
ICES	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$			250	uA
I <sub>GES</sub>	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$			± 100	nA
On Cha	racteristics					
V <sub>GE(th)</sub>	G-E Threshold Voltage	$I_{C}$ = 12mA, $V_{CE}$ = $V_{GE}$	3.5	4.5	6.5	V
	Collector to Emitter	$I_{\rm C} = 12$ A, $V_{\rm GE} = 15$ V		2.1	2.6	V
V <sub>CE(sat)</sub>	Saturation Voltage	$I_{\rm C} = 23$ A, $V_{\rm GE} = 15$ V		2.6		V
			•			
•	c Characteristics	1	1	1	1	
C <sub>ies</sub>	Input Capacitance	V <sub>CE</sub> = 30V, V <sub>GE</sub> = 0V,		720		pF
C <sub>oes</sub>	Output Capacitance	f = 1MHz		100		pF
C <sub>res</sub>	Reverse Transfer Capacitance			25		pF
Tes	•		1	1	1	•
Switchi	ng Characteristics			17	1	
<b>Switchi</b> i t <sub>d(on)</sub>	Turn-On Delay Time			17		ns
<b>Switchii</b> t <sub>d(on)</sub> t <sub>r</sub>	Turn-On Delay Time Rise Time			27		ns
Switchiı t <sub>d(on)</sub> t <sub>r</sub>	Turn-On Delay Time   Rise Time   Turn-Off Delay Time	$V_{CC} = 300 \text{ V}, \text{ I}_{C} = 12\text{ A},$		27 60	 130	ns ns
Switchii t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub>	Turn-On Delay Time     Rise Time     Turn-Off Delay Time     Fall Time	$R_{G} = 23\Omega, V_{GE} = 15V,$	  	27 60 70	 130 150	ns ns ns
Switchii t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> Eon	Turn-On Delay Time     Rise Time     Turn-Off Delay Time     Fall Time     Turn-On Switching Loss			27 60 70 115	 130 150 	ns ns ns uJ
Switchii t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> E <sub>on</sub> E <sub>off</sub>	Turn-On Delay Time     Rise Time     Turn-Off Delay Time     Fall Time     Turn-On Switching Loss     Turn-Off Switching Loss	$R_{G} = 23\Omega, V_{GE} = 15V,$	   	27 60 70 115 135	 130 150  	ns ns ns uJ uJ
<b>Switchii</b> t <sub>d(on)</sub> t <sub>r</sub> t <sub>d(off)</sub> t <sub>f</sub> E <sub>on</sub> E <sub>ts</sub>	Turn-On Delay Time     Rise Time     Turn-Off Delay Time     Fall Time     Turn-On Switching Loss     Turn-Off Switching Loss     Total Switching Loss	$R_{G} = 23\Omega, V_{GE} = 15V,$	    	27 60 70 115 135 250	 130 150  400	ns ns uJ uJ uJ
Switchin d(on) r d(off) df E <sub>off</sub> E <sub>off</sub> E <sub>ts</sub> d(on)	Turn-On Delay Time     Rise Time     Turn-Off Delay Time     Fall Time     Turn-On Switching Loss     Turn-Off Switching Loss     Total Switching Loss     Turn-On Delay Time	$R_{G} = 23\Omega, V_{GE} = 15V,$	   	27 60 70 115 135 250 23	 130 150   400 	ns ns uJ uJ uJ ns
Switchin       tr       tr       td(off)       tf       Eon       Eoff       Ets       td(on)       tr	Turn-On Delay Time     Rise Time     Turn-Off Delay Time     Fall Time     Turn-On Switching Loss     Turn-Off Switching Loss     Total Switching Loss     Turn-On Delay Time     Rise Time	$R_G = 23\Omega$ , $V_{GE} = 15V$ , Inductive Load, $T_C = 25^{\circ}C$	     	27 60 70 115 135 250 23 32	 130 150   400  	ns ns uJ uJ uJ ns ns
Switchin $t_{d(on)}$ $t_r$ $t_d(off)$ $t_d(off)$ $t_d(off)$	Turn-On Delay Time     Rise Time     Turn-Off Delay Time     Fall Time     Turn-On Switching Loss     Turn-Off Switching Loss     Total Switching Loss     Turn-On Delay Time     Rise Time     Turn-Off Delay Time     Turn-Off Delay Time	$R_G = 23\Omega$ , $V_{GE} = 15V$ , Inductive Load, $T_C = 25^{\circ}C$ $V_{CC} = 300$ V, $I_C = 12A$ ,	     	27 60 70 115 135 250 23 32 100	 130 150  400   200	ns ns uJ uJ uJ ns ns ns
Switchin	Turn-On Delay Time     Rise Time     Turn-Off Delay Time     Fall Time     Turn-On Switching Loss     Turn-Off Switching Loss     Total Switching Loss     Turn-On Delay Time     Rise Time     Turn-Off Delay Time     Fall Time     Turn-Off Delay Time     Fall Time	$R_{G} = 23\Omega, V_{GE} = 15V,$ Inductive Load, $T_{C} = 25^{\circ}C$ $V_{CC} = 300 \text{ V}, I_{C} = 12A,$ $R_{G} = 23\Omega, V_{GE} = 15V,$	       	27 60 70 115 135 250 23 32 100 220	 130 150   400  	ns ns uJ uJ uJ ns ns
Switchin $t_{d(on)}$ $t_r$ $t_d(off)$ $t_d(off)$ $t_s$ $t_{d(on)}$ $t_r$ $t_d(on)$ $t_r$ $t_d(off)$ $t_f$ $E_{on}$	Turn-On Delay Time     Rise Time     Turn-Off Delay Time     Fall Time     Turn-On Switching Loss     Total Switching Loss     Total Switching Loss     Turn-On Delay Time     Rise Time     Turn-Off Delay Time     Fall Time     Turn-Off Delay Time     Fall Time     Turn-On Switching Loss	$R_G = 23\Omega$ , $V_{GE} = 15V$ , Inductive Load, $T_C = 25^{\circ}C$ $V_{CC} = 300$ V, $I_C = 12A$ ,	        	27 60 70 115 135 250 23 32 100 220 205	 130 150  400  200 250	ns ns uJ uJ uJ ns ns ns ns uJ
Switchin $t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_{d(off)}$ $t_{d(on)}$ $t_{d(on)}$ $t_{d(on)}$ $t_{d(off)}$ $t_{f}$ $E_{on}$ $E_{off}$	Turn-On Delay Time     Rise Time     Turn-Off Delay Time     Fall Time     Turn-On Switching Loss     Turn-Off Switching Loss     Total Switching Loss     Turn-On Delay Time     Rise Time     Turn-Off Delay Time     Fall Time     Turn-Off Delay Time     Fall Time     Turn-Off Switching Loss     Turn-Off Switching Loss     Turn-Off Switching Loss     Turn-Off Switching Loss	$R_{G} = 23\Omega, V_{GE} = 15V,$ Inductive Load, $T_{C} = 25^{\circ}C$ $V_{CC} = 300 \text{ V}, I_{C} = 12A,$ $R_{G} = 23\Omega, V_{GE} = 15V,$	           	27 60 70 115 250 23 32 100 220 205 320	 130 150  400  200 250  	ns ns uJ uJ uJ ns ns ns ns uJ uJ
Switchin $t_{d(on)}$ $t_r$ $t_{d(off)}$ $t_{f}$ $E_{on}$ $E_{ts}$ $t_{d(on)}$ $t_{r}$ $t_{d(off)}$ $t_{f}$ $E_{on}$	Turn-On Delay Time     Rise Time     Turn-Off Delay Time     Fall Time     Turn-On Switching Loss     Turn-Off Switching Loss     Total Switching Loss     Turn-On Delay Time     Rise Time     Turn-Off Delay Time     Fall Time     Turn-Off Delay Time     Fall Time     Turn-Off Switching Loss     Turn-Off Switching Loss     Turn-Off Switching Loss     Total Switching Loss     Total Switching Loss	$R_{G} = 23\Omega, V_{GE} = 15V,$ Inductive Load, $T_{C} = 25^{\circ}C$ $V_{CC} = 300 V, I_{C} = 12A,$ $R_{G} = 23\Omega, V_{GE} = 15V,$ Inductive Load, $T_{C} = 125^{\circ}C$	            	27 60 70 115 135 250 23 32 100 220 205	 130 150  400  200 250 	ns ns uJ uJ uJ ns ns ns ns uJ uJ uJ
$\begin{array}{c} \textbf{Switchin} \\ \textbf{f}_{d(on)} \\ \textbf{f}_{r} \\ \textbf{f}_{r} \\ \textbf{f}_{d(off)} \\ \textbf{f}_{d(off)} \\ \textbf{f}_{t} \\ \textbf{f}_{ts} \\ \textbf{f}_{d(on)} \\ \textbf{f}_{r} \\ \textbf{f}_{d(off)} \\ \textbf{f}_{t} \\ \textbf{E}_{on} \\ \textbf{E}_{off} \\ \textbf{E}_{off} \\ \textbf{E}_{ts} \\ \textbf{Q}_{g} \end{array}$	Turn-On Delay Time     Rise Time     Turn-Off Delay Time     Fall Time     Turn-On Switching Loss     Turn-Off Switching Loss     Total Switching Loss     Turn-On Delay Time     Rise Time     Turn-Off Delay Time     Fall Time     Turn-Off Delay Time     Fall Time     Turn-Off Switching Loss     Turn-Off Switching Loss     Turn-Off Switching Loss     Total Gate Charge	$R_{G} = 23\Omega, V_{GE} = 15V,$ Inductive Load, $T_{C} = 25^{\circ}C$ $V_{CC} = 300 \text{ V}, I_{C} = 12A,$ $R_{G} = 23\Omega, V_{GE} = 15V,$ Inductive Load, $T_{C} = 125^{\circ}C$ $V_{CE} = 300 \text{ V}, I_{C} = 12A,$	            	27 60 70 115 250 23 32 100 220 205 320 525 49	 130 150  400  200 250   800 80	ns ns uJ uJ uJ ns ns ns ns uJ uJ uJ nC
	Turn-On Delay Time     Rise Time     Turn-Off Delay Time     Fall Time     Turn-On Switching Loss     Turn-Off Switching Loss     Total Switching Loss     Turn-On Delay Time     Rise Time     Turn-Off Delay Time     Fall Time     Turn-Off Delay Time     Fall Time     Turn-Off Switching Loss     Turn-Off Switching Loss     Turn-Off Switching Loss     Total Switching Loss     Total Switching Loss	$R_{G} = 23\Omega, V_{GE} = 15V,$ Inductive Load, $T_{C} = 25^{\circ}C$ $V_{CC} = 300 V, I_{C} = 12A,$ $R_{G} = 23\Omega, V_{GE} = 15V,$ Inductive Load, $T_{C} = 125^{\circ}C$	            	27 60 70 115 250 23 32 100 220 205 320 525	 130 150  400  200 250   800	ns ns uJ uJ uJ ns ns ns ns uJ uJ uJ

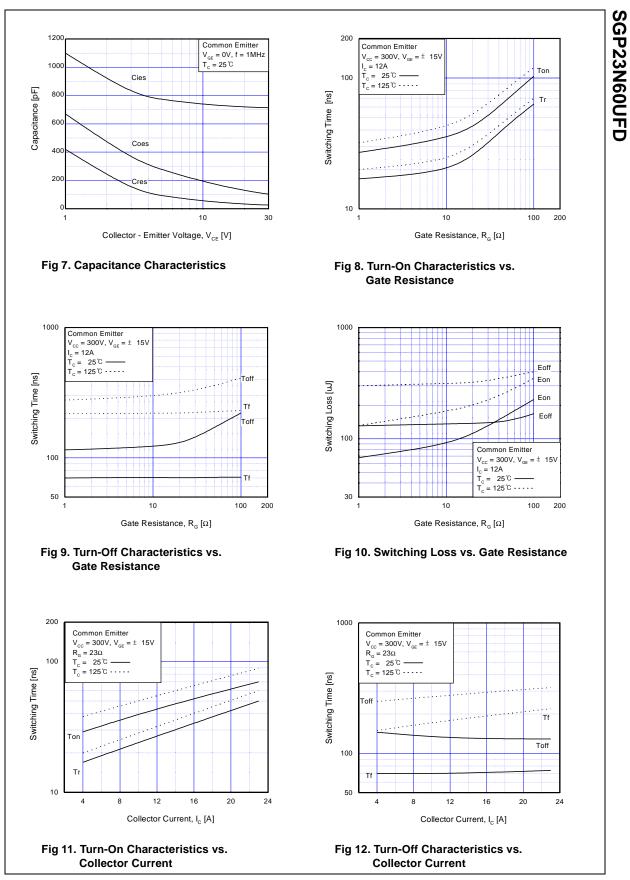
## Electrical Characteristics of DIODE $T_{C} = 25^{\circ}C$ unless otherwise noted

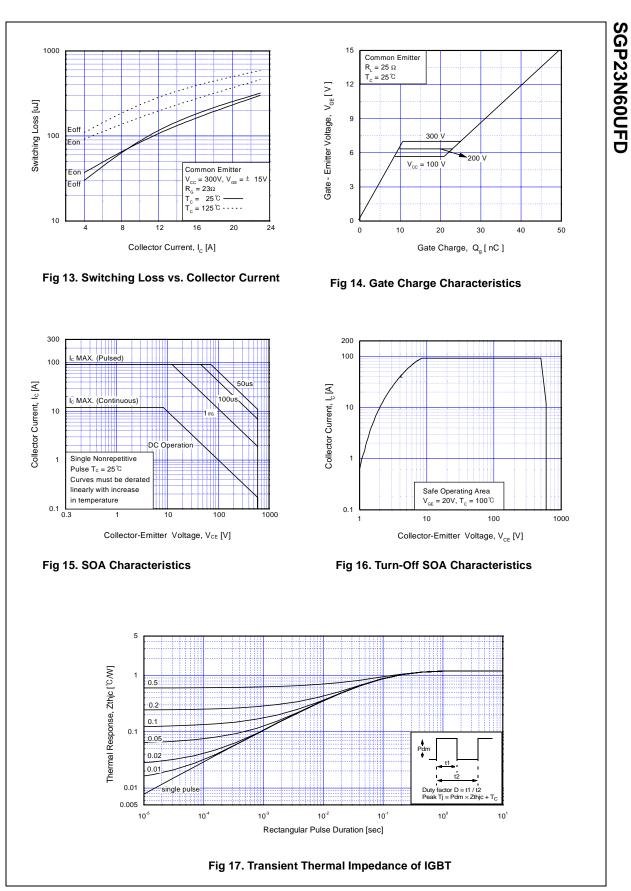
Symbol Parameter		ter Test Conditions		Min.	Тур.	Max.	Units
V	Diada Farward Valtaga	1 - 124	$T_{C} = 25^{\circ}C$		1.4	1.7	V
V <sub>FM</sub> Diode Forward Voltage	Diode Forward Voltage I <sub>F</sub> = 12A	$T_{C} = 100^{\circ}C$		1.3		v	
		$T_{C} = 25^{\circ}C$		42	60	20	
t <sub>rr</sub>	T Diode Reverse Recovery Time		$T_{C} = 100^{\circ}C$		80		ns
1	Diode Peak Reverse Recovery	I <sub>F</sub> = 12A, di/dt = 200A/us	$T_{C} = 25^{\circ}C$		3.5	6.0	Α
rr	Current		$T_{C} = 100^{\circ}C$		5.6		A
Q <sub>rr</sub> Diode	Diode Reverse Recovery Charge		$T_{C} = 25^{\circ}C$		80	180	nC
			T <sub>C</sub> = 100°C		220		iiC

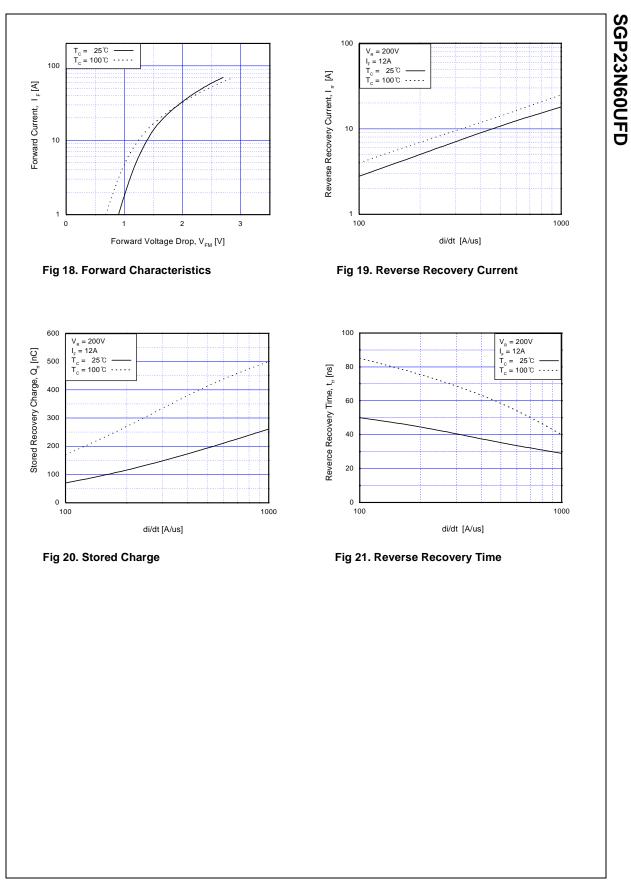
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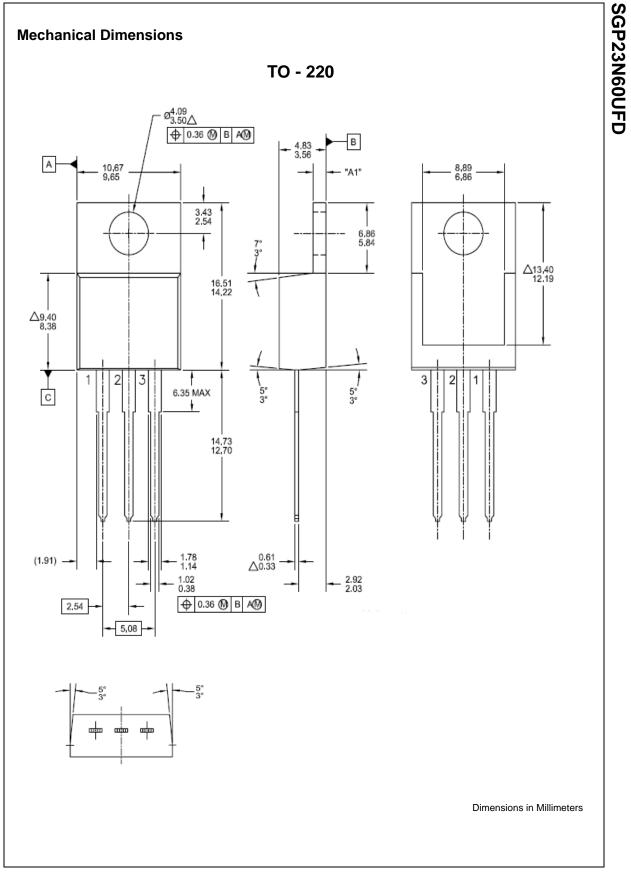
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